

## ABSTRACT

The invention relates to a conductor crossover for a semiconductor detector, particularly for a drift detector for conducting X-ray spectroscopy. The conductor crossover comprises at least two doped semiconductor electrodes (2), which are placed inside a semiconductor substrate 5 (1), at least one connecting conductor (M), which is guided over the semiconductor electrodes (2), and a first insulating layer (Ox). An intermediate electrode (L) is situated between the connecting conductor (M) and the first insulation layer (Ox). Said intermediate electrode overlaps the area of the semiconductor substrate (1) between the semiconductor electrodes (2) and is electrically insulated from the connecting conductor (M) by at least one additional 10 insulation layer (I). The invention also relates to a drift detector equipped with a conductor crossover of this type and to a detector arrangement for conducting X-ray spectroscopy.